

GPDP3260

RECTIFIER DIODE

VOLTAGE UP TO	2200 V
AVERAGE CURRENT	2600 A
SURGE CURRENT	31 kA

BLOCKING CHARACTERISTICS

Characteristic		Conditions	Value
VRRM	Repetitive peak reverse voltage		2200 V
VRSM	Non-repetitive peak reverse voltage		2200 V
IRRM	Repetitive peak reverse current, max.	VRRM, single phase, half wave, T _j = 175 °C	100 mA

FORWARD CHARACTERISTICS

I _{F(AV)}	Average forward current	Sine wave, 180° conduction, T _c = 100°C	2600 A
I _{F(RMS)}	R.M.S. forward current	Sine wave, 180° conduction, T _c = 100°C	4084 A
I _{FSM}	Surge forward current	Non rep. half sine wave, 50 Hz, V _R = 0 V, T _j = T _{jmax}	31 kA
I ² t	I ² t for fusing coordination		4805 kA ² s
V _{F(TO)}	Threshold voltage	T _j = T _{jmax}	0,79 V
r _F	Forward slope resistance	T _j = T _{jmax}	0,115 mΩ
V _{FM}	Peak forward voltage, max	Forward current I _F = 4000 A, T _j = 25°C	1,22 V

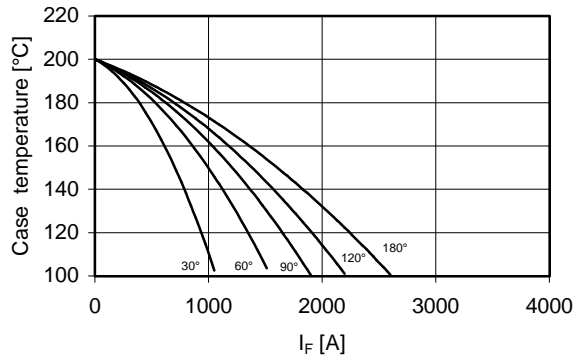
SWITCHING CHARACTERISTICS

Q _{rr}	Reverse recovery charge, typ	T _j = T _{jmax} , I _F = 2000 A, di/dt = -5 A/μs V _R = 100 V	1900 μC
I _{rr}	Reverse recovery current		A
t _{rr}	Reverse recovery time		μs
V _{FP}	Forward recovery voltage	T _j = T _{jmax} , di/dt = A/μs	V

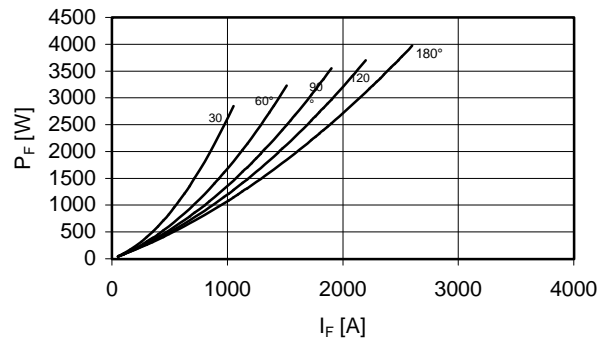
THERMAL AND MECHANICAL CHARACTERISTICS

R _{th(j-c)}	Thermal resistance (junction to case)	Double side cooled	0,024 °C/W
R _{th(c-h)}	Thermal resistance (case to heatsink)	Double side cooled	0,001 °C/W
T _{jmax}	Max operating junction temperature		200 °C
T _{stg}	Storage temperature		-40 / 200 °C
F	Clamping force ± 10%		22 kN
	Mass		500 g

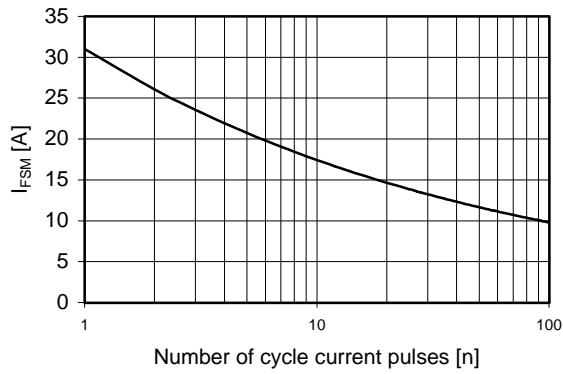
Current rating - sine wave



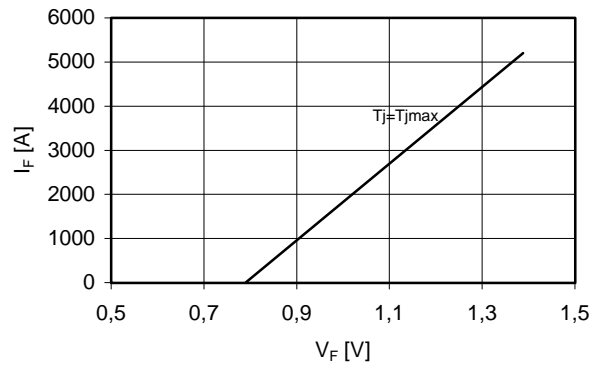
Power loss - sine wave



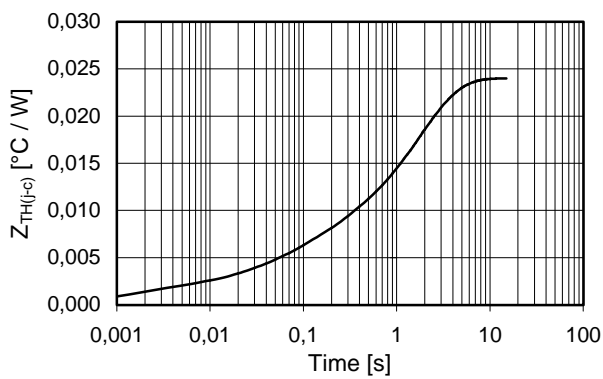
Maximum surge current
d.s. cooled



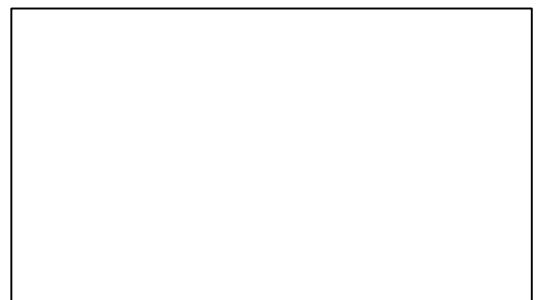
Forward voltage drop



Thermal Impedance (j-c)



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